

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently Amended) A group III nitride compound semiconductor light-emitting device, comprising:

a semiconductor laminate portion including a light-emitting layer; and

a reflection surface disposed so as to be opposite to a side surface of said light-emitting layer semiconductor laminate portion,

wherein said semiconductor laminate portion and said reflection surface are provided in ~~one~~ and the same chip.

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Claim 2. (Original) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light from said side surface of said semiconductor laminate portion into a direction of an optical axis of said light-emitting device.

Claim 3. (Original) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of from 0.1 to 10 μ m.

Claim 4. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises ~~is made of~~ a material which is the same as that of an n pad electrode.

Claim 5. (Original) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein a portion of said n pad electrode opposite to said side surface of said semiconductor laminate portion from a second reflection surface.

Claim 6. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed on an n-type semiconductor layer which is formed by etching to ~~be~~ a first depth, and said n pad electrode is

formed on said n-type semiconductor layer which is formed by etching to be a second depth shallower than said first depth.

Claim 7. (Original) A group II nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed integrally with said n pad electrode.

Claim 8. (Currently Amended) A group III nitride compound semiconductor light-emitting device, comprising:

a plurality laminate of group III nitride compound semiconductor layers comprising inclusive of a light-emitting layer;

a groove formed in said plurality of group III nitride compound semiconductor layers laminate; and

a reflection surface formed on an outer side surface of said groove, said reflection surface being disposed opposite to a side surface of said light-emitting layer.

Claim 9. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said groove is formed by a dicing saw.

Claim 10. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said reflection surface comprises ~~is made of~~ a metal layer.

Claim 11. (Currently Amended) A group III nitride compound semiconductor light-emitting device according to claim 10, wherein said metal layer comprises ~~is made of~~ a material which is the same as that of an n pad electrode, and said metal layer is formed at the same time when said n pad electrode is formed.

Claim 12. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein light emitted from a side surface of said laminate is reflected by said reflected surface in a direction of an optical axis of said light-emitting device.

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Claim 13. (Currently Amended) A group nitride compound semiconductor light-emitting device according to claim 8, wherein said plurality of group III nitride compound semiconductor layers further comprises a substrate, a bottom of said groove being defined by said ~~has a depth to reach a~~ substrate.

Claim 14. (Original) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein said groove is substantially parallel to a chip cutting line.

Claim 15. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of 0.2 μm to 7 μm .

Claim 16. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a distance between said reflection surface and said side surface of said semiconductor laminate portion is in a range of 0.3 μm to 5 μm .

Claim 17. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is formed on a layer in said semiconductor laminate portion.

Claim 18. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein an upper surface of said reflection surface is elevated higher than said light-emitting layer.

Claim 19. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a curved reflection surface.

Claim 20. (New) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein a width of said groove is in a range of 3 μm to 50 μm .

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Claim 21. (New) A group III nitride compound semiconductor light-emitting device according to claim 8, wherein a width of said groove is in a range of 7 μm to 40 μm .

Claim 22. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein at least a portion of said reflector surface lies in a same plane as a portion of said light-emitting layer.
